

FORM PTO-1449 US Dept. of Commerce Patent and Trademark Office				ATTORNEY DOCKET NO.		SERIAL NO.	
				ATMI-272-CIP		09/874,102	
INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)				APPLICANT			
				Peter C. Van Buskirk, et al.		FILING DATE	
				June 5, 2001		GROUP 1761 1763	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Xiao	AA	08/975,366 5,976,928	11/1999	Van Buskirk and Kirlin			11/20/98
	AB	6,018,065	1/2/00	Baum, et al.			
	AC	5,911,887	6/15/99	Smith, et al.			
	AD	5,814,238	9/29/98	Ashby, et al.			
Xiao	AE	4,659,426	4/21/87	Fuller, et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)							
Xiao	AF	Koteki, D.E., "A Review of High Dielectric Materials for DRAM Capacitors", <i>Integ. Ferro.</i> , 1997, Vol. 16, pp. 1-19.					
	AG	Jeon, et al., "Thermal Stability of Ir/Polycrystalline-Si Structure for Bottom Electrode of Integrated Ferroelectric Capacitors", <i>Appl. Physics Lett.</i> , 1997, Vol. 71(4), pp. 467-469.					
	AH	Williams, et al., "Etch Rates for Micromachining Processing", <i>Journ. For Microelectromechanical Systems</i> , December 1996, Vol. 5 (4), pp. 256-269					
	AI	Vugts, et al., "Si/XeF ₂ Etching-Temperature Dependence", 1996, <i>J. Vac. Sci. Tech. A</i> , Vol. 14(5), pp. 2766-2774					
	AJ	P.C. Fazan, et al., "Stacked Capacitor Modules for 64 Mb DRAMs and Beyond", <i>Semiconductor Inter.</i> , 1992, Vol. 108, pp. 108-112					
Xiao	AK	L. H. Parker, et al., Ferroelectric Materials for 64Mb and 256Mb DRAMs", <i>IEEE Circuits and Devices Mag.</i> , Jan. 1990, pp. 17-26					
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EXAMINER <i>Xiao</i>				DATE CONSIDERED <i>12/11/03</i>			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							

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<i>(Handwritten notes and several horizontal lines drawn through the table rows.)</i>							
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OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)							
<i>AA</i>	BA	R. E. Sievers, et al., "Volatile Barium B-Diketonates for Use as MOCVD Precursors", <i>Coord. Chem. Rev.</i> , 1993, pp. 285-291.					
	BB	C. Farrell, et al., "A Reactive Ion Etch Study for Producing Patterned Platinum Structures", Presented at ISIF 96, March 18, 19, 20, 1996 Tempe AZ. (to be published in <i>Integrated Ferroelectrics</i>).					
	BC	K. R. Milkove and C. X. Wang, "Insight into the dry cleaning of Fence Patterned Platinum Structures", <i>J. Vac. Sci. Tech. A</i> , 1997, Vol. 15(3), pp. 596-603					
	BD	Chang, F.I., et al., "Gas Phase Silicon Micromachining with Xenon Difluoride", <i>Proc of SPIE</i> , 1995, Vol. 2641, pp. 117-128.					
	BE	Bensaola, A. et al., "Low Temperature Ion Beam Enhanced Etching of Tungsten Films with Xenon Difluoride", <i>Appl. Phys. Lett.</i> , Dec. 1986, Vol. 49(24), pp. 1663-1664					
<i>AA</i>	BF	G. Stauf, "BaSrTiO ₃ Etching for Advanced Microelectronic Devices, U.S. Army Missile Command, Report Number, DAAH01-96-C-R035, 1/10/96-1/30/98.					
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EXAMINER <i>Allen e. Olsen</i>				DATE CONSIDERED <i>12/11/03</i>			
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<i>Ans</i>	CA	Ebsworth, E.A.V., et al., "Formation of Iridium Fluoroacyl Complexes by Reaction of Iridium Carbonyls with Xenon Difluoride and Reactions of these to Generate Unusual Acyl Complexes", <i>J. Chem. Soc., Dalton Trans.</i> , 1993, ISS. 7, pp. 1031-7					
<i>Ans</i>	CB	Blake, A.J., et al., " Novel Reaction of an Iridium Carbonyl Complex with Xenon Difluoride: The First Metal Fluoroacyl Complex", <i>J. Chem. Soc., Chem. Commun.</i> , 1988, ISS.8, pp. 529-530					
	CC	Sladkey, F.O., et al., " Xenon Difluoride as a Fluoride Ion Donor" <i>J. Chem. Soc. A</i> , 1969, Vol. 14, pp. 2179-88					
<i>Ans</i>	CD	Floy I. Chang, et al., Gas-Phase Silicon Micromachining with Xenon Difluoride, Proc. Of SPIE vol. 2641, pp. 117-128.					
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EXAMINER	<i>John A. O'Conor</i>			DATE CONSIDERED			
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